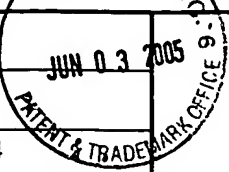


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| First Named Inventor | Leonard Forbes |  | INFORMATION DISCLOSURE STATEMENT |
| Serial No. | 10/808,059 | | |
| Filing Date | March 24, 2004 | | |
| Group Art Unit | 2814 | | |
| Examiner Name | Marcos D. Pizarro Crespo | | |
| Confirmation No. | 4221 | | |
| Attorney Docket No. | 400.285US01 | | |
| Title: NROM MEMORY DEVICE WITH HIGH-PERMITTIVITY GATE DIELECTRIC FORMED BY THE LOW TEMPERATURE OXIDIZATION OF METALS | | | |

Mail Stop: AMENDMENT
 Commissioner for Patents
 P.O. Box 1450
 Alexandria, VA 22313-1450

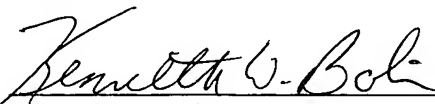
In compliance with 37 C.F.R. §§ 1.56 and 1.97, *et seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified Application. Pursuant to 37 C.F.R. 1.98 (a)(2)(i), as this application was filed after June 30, 2003, Applicant has not included copies of U.S. Patents or U.S. Patent Applications. Applicant respectfully requests that this Information Disclosure Statement be entered and the references listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to MPEP §609, Applicant further requests that the Examiner initial next to each reference on the Form 1449 to indicate that the listed references have been considered. Applicant further requests that a copy of the initialed Form 1449 be returned with the next official communication.

As an Office Action has not yet issued in this application, Applicant believes that no fees are due. However, the Commissioner for Patents is hereby authorized to charge any additional fees to Deposit Account No. 501373.

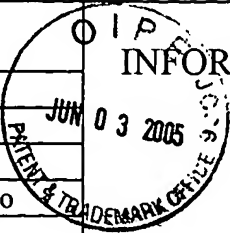
If the Examiner has any questions or concerns regarding this application, please contact the undersigned at (612) 312-2211.

Respectfully submitted,

Date: 5/31/05


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| First Named Inventor | Leonard Forbes |  <p>INFORMATION DISCLOSURE STATEMENT FORM PTO-1449</p> |
| Serial No. | 10/808,059 | |
| Filing Date | March 24, 2004 | |
| Group Art Unit | 2814 | |
| Examiner Name | M. D. Pizarro Crespo | |
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| Sheet 1 of 1 | | |

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| Examiner Initials | Foreign Patent | | Name | Publication Date | Translation |
| | Country | No. | | | |
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|-------------------|---|
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|--|--|-----------------|--|
| Examiner Signature | | Date Considered | |
| *Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. | | | |